

DRAM

**MT4LC4M4B1, MT4C4M4B1
MT4LC4M4A1, MT4C4M4A1**

For the latest data sheet, please refer to the Micron Web site: www.micronsemi.com/mti/msp/html/datasheet.html

FEATURES

- Industry-standard x4 pinout, timing, functions, and packages
- High-performance, low-power CMOS silicon-gate process
- Single power supply ($+3.3V \pm 0.3V$ or $+5V \pm 0.5V$)
- All inputs, outputs and clocks are TTL-compatible
- Refresh modes: RAS#-ONLY, HIDDEN and CAS#-BEFORE-RAS# (CBR)
- Optional self refresh (S) for low-power data retention
- 11 row, 11 column addresses (2K refresh) or 12 row, 10 column addresses (4K refresh)
- FAST-PAGE-MODE (FPM) access
- 5V tolerant inputs and I/Os on 3.3V devices

OPTIONS

- | | |
|-----------------------------|------|
| Voltage | LC |
| 3.3V | C |
| 5V | |
| Refresh Addressing | B1 |
| 2,048 (2K) rows | A1 |
| 4,096 (4K) rows | |
| Packages | DJ |
| Plastic SOJ (300 mil) | TG |
| Plastic TSOP (300 mil) | |
| Timing | -5 |
| 50ns access | |
| 60ns access | -6 |
| Refresh Rates | None |
| Standard Refresh | S* |
| Self Refresh (128ms period) | |

NOTE: 1. The 4 Meg x 4 FPM DRAM base number differentiates the offerings in one place—MT4LC4M4B1. The fifth field distinguishes various options: B1 designates a 2K refresh and A1 designates a 4K refresh for FPM DRAMs.

2. The # symbol indicates signal is active LOW.

*Contact factory for availability

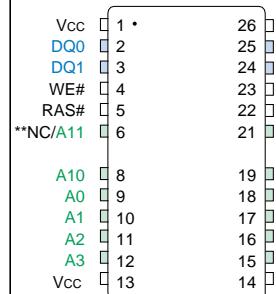
Part Number Example:
MT4LC4M4B1DJ

KEY TIMING PARAMETERS

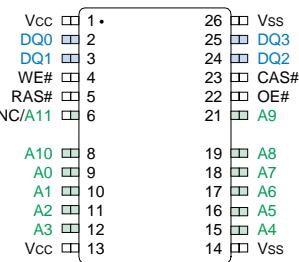
SPEED	t _{RC}	t _{RAC}	t _{PC}	t _{AA}	t _{CAC}	t _{RP}
-5	84ns	50ns	20ns	25ns	13ns	30ns
-6	110ns	60ns	35ns	30ns	15ns	40ns

PIN ASSIGNMENT (Top View)

24/26-Pin SOJ



24/26-Pin TSOP



**NC on 2K refresh and A11 on 4K refresh options.

4 MEG x 4 FPM DRAM PART NUMBERS

PART NUMBER	V _{CC}	REFRESH ADDRESSING	PACKAGE	REFRESH
MT4LC4M4B1DJ-6	3.3V	2K	SOJ	Standard
MT4LC4M4B1DJ-6S	3.3V	2K	SOJ	Self
MT4LC4M4B1TG-6	3.3V	2K	TSOP	Standard
MT4LC4M4B1TG-6S	3.3V	2K	TSOP	Self
MT4LC4M4A1DJ-6	3.3V	4K	SOJ	Standard
MT4LC4M4A1DJ-6S	3.3V	4K	SOJ	Self
MT4LC4M4A1TG-6	3.3V	4K	TSOP	Standard
MT4C4M4A1TG-6S	3.3V	4K	TSOP	Self
MT4C4M4B1DJ-6	5V	2K	SOJ	Standard
MT4C4M4B1DJ-6S	5V	2K	SOJ	Self
MT4C4M4B1TG-6	5V	2K	TSOP	Standard
MT4C4M4B1TG-6S	5V	2K	TSOP	Self
MT4C4M4A1DJ-6	5V	4K	SOJ	Standard
MT4C4M4A1DJ-6S	5V	4K	SOJ	Self
MT4C4M4A1TG-6	5V	4K	TSOP	Standard
MT4C4M4A1TG-6S	5V	4K	TSOP	Self

GENERAL DESCRIPTION

The 4 Meg x 4 DRAM is a randomly accessed, solid-state memory containing 16,777,216 bits organized in a x4 configuration. RAS# is used to latch the row address (first 11 bits for 2K and first 12 bits for 4K). Once the page has been opened by RAS#, CAS# is used to latch the column address (the latter 11 bits for 2K and the latter 10 bits for 4K; address pins A10 and A11 are "Don't Care").

READ and WRITE cycles are selected with the WE# input. A logic HIGH on WE# dictates read mode, while a logic LOW on WE# dictates write mode. During a WRITE cycle, data-in (D) is latched by the falling edge of WE# or CAS#, whichever occurs last. If WE# goes LOW prior to CAS# going LOW, the output pins remain open (High-Z) until the next CAS# cycle, regardless of OE#.

A logic HIGH on WE# dictates read mode, while a logic LOW on WE# dictates write mode. During a WRITE cycle, data-in (D) is latched by the falling edge of WE# or CAS#, whichever occurs last. An EARLY WRITE occurs when WE# is taken LOW prior to CAS# falling. A LATE WRITE or READ-MODIFY-WRITE occurs when WE# falls after CAS# is taken LOW. During EARLY WRITE cycles, the data outputs (Q) will remain High-Z regardless of the state of OE#. During LATE WRITE or READ-MODIFY-WRITE cycles, OE# must be taken HIGH to disable the data outputs prior to applying input data. If a LATE WRITE or READ-MODIFY-WRITE is attempted while keeping OE# LOW, no WRITE will occur, and the data outputs will drive read data from the accessed location.

The four data inputs and the four data outputs are routed through four pins using common I/O, and pin direction is controlled by WE# and OE#.

The MT4LC4M4B1 and MT4LC4M4A1 must be refreshed periodically in order to retain stored data.

FAST PAGE MODE ACCESS

Page operations allow faster data operations (READ, WRITE or READ-MODIFY-WRITE) within a row-address-defined page boundary. The page cycle is always initiated with a row address strobed in by RAS#, followed by a column address strobed in by CAS#.

Additional columns may be accessed by providing valid column addresses, strobing CAS# and holding RAS# LOW, thus executing faster memory cycles. Returning RAS# HIGH terminates the page mode of operation, i.e., closes the page.

DRAM REFRESH

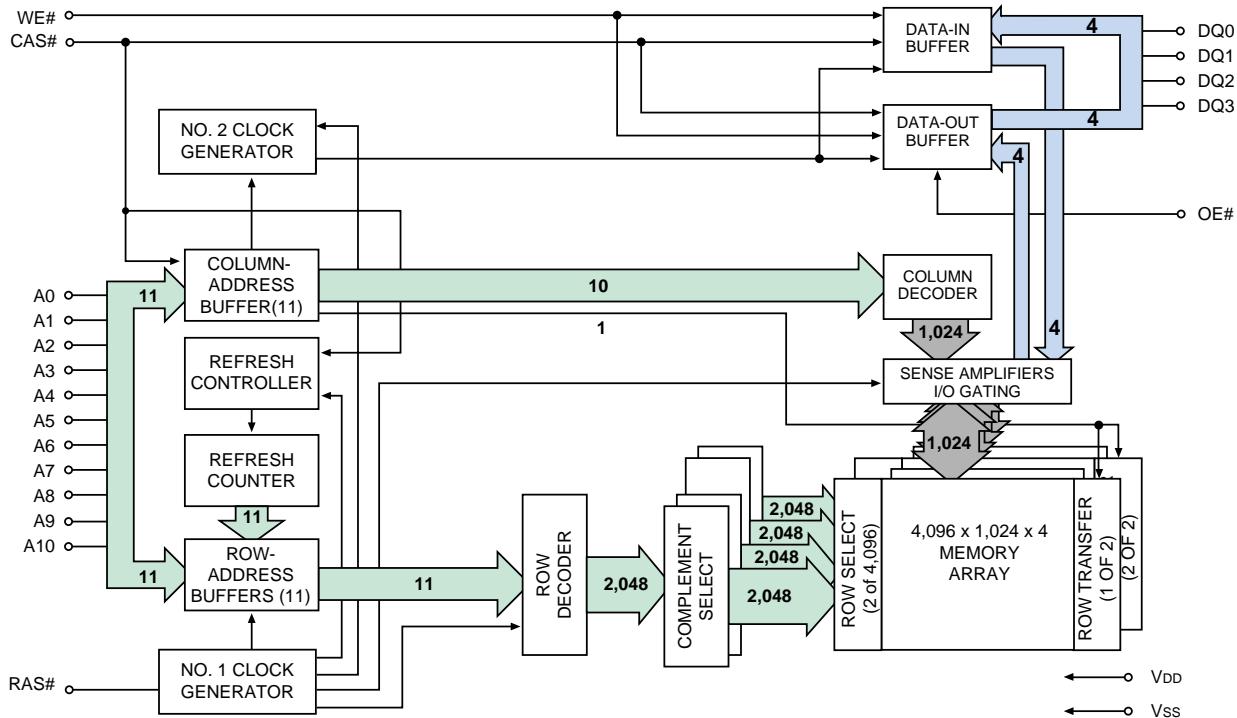
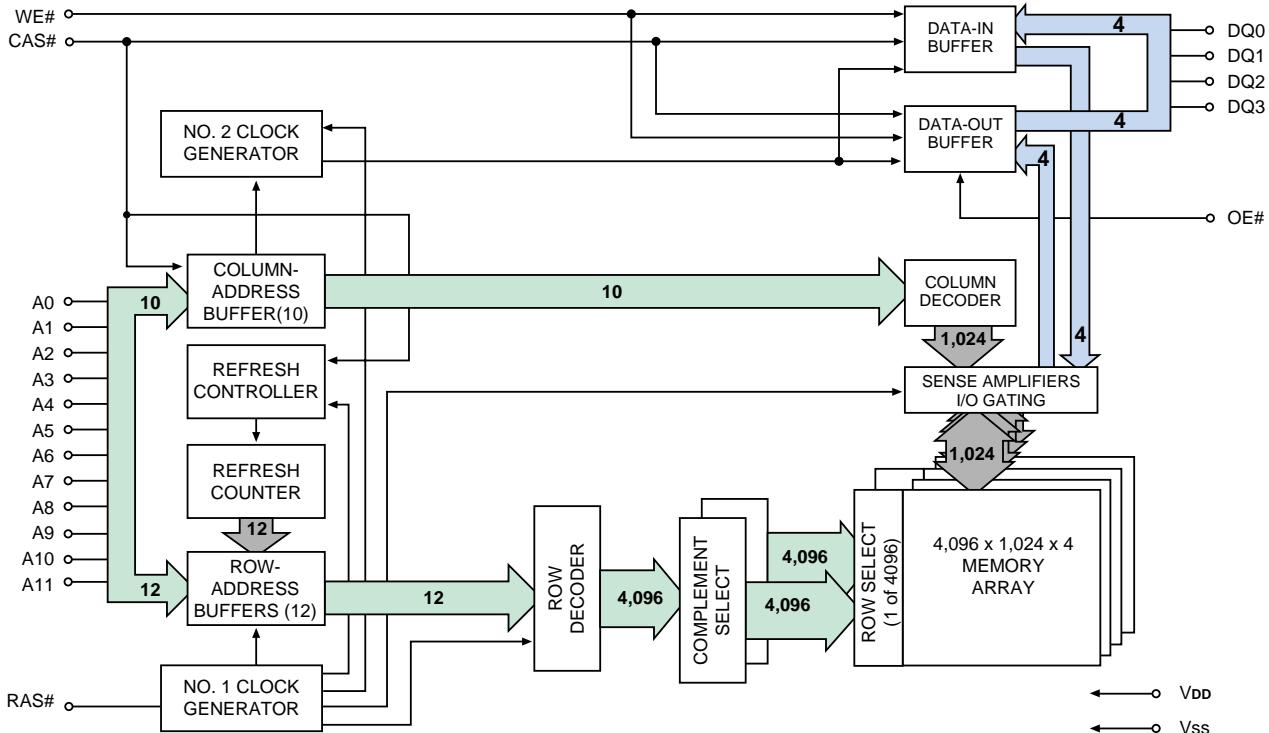
Preserve correct memory cell data by maintaining power and executing any RAS# cycle (READ, WRITE) or RAS# REFRESH cycle (RAS#-ONLY, CBR, or HID-DEN) so that all combinations of RAS# addresses (2,048 for 2K and 4,096 for 4K) are executed within $t_{REF}^{(MAX)}$, regardless of sequence. The CBR and SELF REFRESH cycles will invoke the internal refresh counter for automatic RAS# addressing.

An optional self refresh mode is also available the "S" version. The self refresh feature is initiated by performing a CBR REFRESH cycle and holding RAS# LOW for the specified t_{RASS} . The "S" option allows the user the choice of a fully static, low-power data retention mode or a dynamic refresh mode at the extended refresh period of 128ms, or 31.25 μ s per row for a 4K refresh and 62.5 μ s per row for a 2K refresh, when using a distributed CBR REFRESH. This refresh rate can be applied during normal operation, as well as during a standby or battery backup mode.

The self refresh mode is terminated by driving RAS# HIGH for a minimum time of t_{RPS} . This delay allows for the completion of any internal refresh cycles that may be in process at the time of the RAS# LOW-to-HIGH transition. If the DRAM controller uses a distributed CBR refresh sequence, a burst refresh is not required upon exiting self refresh. However, if the DRAM controller utilizes RAS#-ONLY or burst CBR refresh sequence, all rows must be refreshed with a refresh rate of t_{RC} minimum prior to resuming normal operation.

STANDBY

Returning RAS# and CAS# HIGH terminates a memory cycle and decreases chip current to a reduced standby level. The chip is preconditioned for the next cycle during the RAS# HIGH time.

FUNCTIONAL BLOCK DIAGRAM – 2K REFRESH

FUNCTIONAL BLOCK DIAGRAM – 4K REFRESH


ABSOLUTE MAXIMUM RATINGS*

Voltage on VCC Pin Relative to VSS

 3.3V..... -1V to +4.6V
 5V..... -1V to +7V

Voltage on NC, Inputs or I/O Pins Relative to VSS

 3.3V..... -1V to +5.5V
 5V..... -1V to +7V

 Operating Temperature, T_A (ambient) 0°C to +70°C

Storage Temperature (plastic) -55°C to +150°C

Power Dissipation 1W

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS AND OPERATING CONDITIONS

 (Notes: 5, 6) ($V_{CC}(\text{MIN}) \leq V_{CC} \leq V_{CC}(\text{MAX})$)

PARAMETER/CONDITION	SYMBOL	3.3V		5V		UNITS	NOTES
		MIN	MAX	MIN	MAX		
SUPPLY VOLTAGE	V_{CC}	3	3.6	4.5	5.5	V	
INPUT HIGH VOLTAGE: Valid Logic 1; All inputs, I/Os and any NC	V_{IH}	2	5.5	2.4	$V_{CC}+1$	V	24
INPUT LOW VOLTAGE: Valid Logic 0; All inputs, I/Os and any NC	V_{IL}	-1.0	0.8	-0.5	0.8	V	24
INPUT LEAKAGE CURRENT: Any input at V_{IN} [$0V \leq V_{IN} \leq V_{CC}(\text{MAX})$]; All other pins not under test = 0V	I_I	-2	2	-2	2	μA	
OUTPUT HIGH VOLTAGE: $I_{OUT} = -2mA$	V_{OH}	2.4	-	2.4	-	V	
OUTPUT LOW VOLTAGE: $I_{OUT} = 2mA$	V_{OL}	-	0.4	-	0.4	V	
OUTPUT LEAKAGE CURRENT: Any output at V_{OUT} [$0V \leq V_{OUT} \leq V_{CC}(\text{MAX})$]; DQ is disabled and in High-Z state	I_{OZ}	-5	5	-5	5	μA	

I_{cc} OPERATING CONDITIONS AND MAXIMUM LIMITS

(Notes: 1, 2, 3, 5, 6) [V_{CC} (MIN) ≤ V_{CC} ≤ V_{CC} (MAX)]

PARAMETER/CONDITION	SYM	SPEED	3.3V		5V		UNITS	NOTES
			2K REFRESH	4K REFRESH	2K REFRESH	4K REFRESH		
STANDBY CURRENT:TTL (RAS# = CAS# = V _{IH})	I _{CC1}	ALL	1	1	1	1	mA	
STANDBY CURRENT:CMOS(non-“S” version only) (RAS# = CAS# = other inputs = V _{CC} - 0.2V)	I _{CC2}	ALL	500	500	500	500	mA	
STANDBY CURRENT:CMOS(“S” version only) (RAS# = CAS# = other inputs = V _{CC} - 0.2V)	I _{CC2}	ALL	150	150	150	150	µA	
OPERATING CURRENT:Random READ/WRITE Average power supply current (RAS#, CAS#, address cycling: t _{RC} = t _{RC} [MIN])	I _{CC3}	-5 -6	110 100	90 80	140 130	120 110	mA	23
OPERATING CURRENT:FAST PAGE MODE Average power supply current (RAS# = V _{IL} , CAS#, address cycling: t _{PC} = t _{PC} [MIN])	I _{CC4}	-5 -6	110 100	100 90	110 100	100 90	mA	23
REFRESH CURRENT:RAS#-ONLY Average power supply current (RAS# cycling, CAS# = V _{IH} ; t _{RC} = t _{RC} [MIN])	I _{CC5}	-5 -6	110 100	90 80	140 130	120 110	mA	
REFRESH CURRENT:CBR Average power supply current (RAS#, CAS#, address cycling: t _{RC} = t _{RC} [MIN])	I _{CC6}	-5 -6	110 100	90 80	140 130	120 110	mA	4, 7
REFRESH CURRENT:Extended (“S” version only) Average power supply current: CAS# = 0.2V or CBR cycling; RAS# = t _{RAS} (MIN); WE# = V _{CC} - 0.2V; A0-A11, OE# and D _{IN} = V _{CC} - 0.2V or 0.2V (D _{IN} may be left open)	I _{CC7}	ALL t _{RC}	300 62.5	300 31.25	300 62.5	300 31.25	µA µs	4, 7 23
REFRESH CURRENT:Self (“S” version only) Average power supply current: CBR with RAS# ≥ t _{RASS} (MIN) and CAS# held LOW; WE# = V _{CC} - 0.2V; A0-A11, OE# and D _{IN} = V _{CC} - 0.2V or 0.2V (D _{IN} may be left open)	I _{CC8}	ALL	300	300	300	300	µA	4, 7

CAPACITANCE

(Note: 6)

PARAMETER	SYMBOL	MAX	UNITS
Input Capacitance: Address pins	C _{I1}	5	pF
Input Capacitance: RAS#, CAS#, WE#, OE#	C _{I2}	7	pF
Input/Output Capacitance: DQ	C _{IO}	7	pF

AC ELECTRICAL CHARACTERISTICS

(Notes: 5, 6, 7, 8, 9, 10, 11, 12) [Vcc (MIN) ≤ Vcc ≤ Vcc (MAX)]

AC CHARACTERISTICS			-5		-6			
PARAMETER	SYMBOL		MIN	MAX	MIN	MAX	UNITS	NOTES
Access time from column address	t_{AA}			25		30	ns	
Column-address hold time (referenced to RAS#)	t_{AR}	38		45			ns	
Column-address setup time	t_{ASC}	0		0			ns	
Row-address setup time	t_{ASR}	0		0			ns	
Column address to WE# delay time	t_{AWD}	42		49			ns	18
Access time from CAS#	t_{CAC}			13		15	ns	
Column-address hold time	t_{CAH}	8		10			ns	
CAS# pulse width	t_{CAS}	8	10,000	10	10,000		ns	
CAS# LOW to "Don't Care" during Self Refresh	t_{CHD}	15		15			ns	
CAS# hold time (CBR Refresh)	t_{CHR}	8		10			ns	4
CAS# to output in Low-Z	t_{CLZ}	0		0			ns	22
CAS# precharge time	t_{CP}	8		10			ns	13
Access time from CAS# precharge	t_{CPA}		28			35	ns	
CAS# to RAS# precharge time	t_{CRP}	5		5			ns	
CAS# hold time	t_{CSH}	38		45			ns	
CAS# setup time (CBR Refresh)	t_{CSR}	5		5			ns	4
CAS# to WE# delay time	t_{CWD}	28		35			ns	18
WRITE command to CAS# lead time	t_{CWL}	8		10			ns	
Data-in hold time	t_{DH}	8		10			ns	19
Data-in setup time	t_{DS}	0		0			ns	19
Output disable	t_{OD}	0	12	0	15		ns	22
Output enable	t_{OE}		12			15	ns	20
OE# hold time from WE# during READ-MODIFY-WRITE cycle	t_{OEH}	8		10			ns	
Output buffer turn-off delay	t_{OFF}	0	12	0	15		ns	17, 22
OE# setup prior to RAS# during HIDDEN REFRESH cycle	t_{ORD}	0		0			ns	
FAST-PAGE-MODE READ or WRITE cycle time	t_{PC}	20		25			ns	
FAST-PAGE-MODE READ-WRITE cycle time	t_{PRWC}	47		56			ns	
Access time from RAS#	t_{RAC}		50			60	ns	
RAS# to column-address delay time	t_{RAD}	9		12			ns	15
Row-address hold time	t_{RAH}	9		10			ns	
RAS# pulse width	t_{RAS}	50	10,000	60	10,000		ns	
RAS# pulse width (FAST PAGE MODE)	t_{RASP}	50	125,000	60	125,000		ns	
RAS# pulse width during Self Refresh	t_{RASS}	100		100			μs	
Random READ or WRITE cycle time	t_{RC}	84		104			ns	
RAS# to CAS# delay time	t_{RCD}	11		14			ns	14
READ command hold time (referenced to CAS#)	t_{RCH}	0		0			ns	16
READ command setup time	t_{RCS}	0		0			ns	
Refresh period (2,048 cycles)	t_{REF}		32		32		ms	
Refresh period (4,096 cycles)	t_{REF}		64		64		ms	

AC ELECTRICAL CHARACTERISTICS

(Notes: 5, 6, 7, 8, 9, 10, 11, 12) [Vcc (MIN) ≤ Vcc ≤ Vcc (MAX)]

AC CHARACTERISTICS			-5		-6			
PARAMETER	SYMBOL		MIN	MAX	MIN	MAX	UNITS	NOTES
Refresh period "S" version	t_{REF}			128		128	ms	140
RAS# precharge time	t_{RP}	30		40			ns	
RAS# to CAS# precharge time	t_{RPC}	5		5			ns	
RAS# precharge time exiting Self Refresh	t_{RPS}	90		105			ns	
READ command hold time (referenced to RAS#)	t_{RRH}	0		0			ns	16
RAS# hold time	t_{RSR}	13		15			ns	
READ-WRITE cycle time	t_{RWC}	116		140			ns	
RAS# to WE# delay time	t_{RWD}	67		79			ns	19
WRITE command to RAS# lead time	t_{RWL}	13		15			ns	
Transition time (rise or fall)	t_T	2	50	2	50		ns	
WRITE command hold time	t_{WCH}	8		10			ns	
WRITE command hold time (referenced to RAS#)	t_{WCR}	38		45			ns	
WE# command setup time	t_{WCS}	0		0			ns	18
WRITE command pulse width	t_{WP}	5		5			ns	
WE# hold time (CBR Refresh)	t_{WRH}	8		10			ns	4, 23
WE# setup time (CBR Refresh)	t_{WRP}	8		10			ns	4, 23

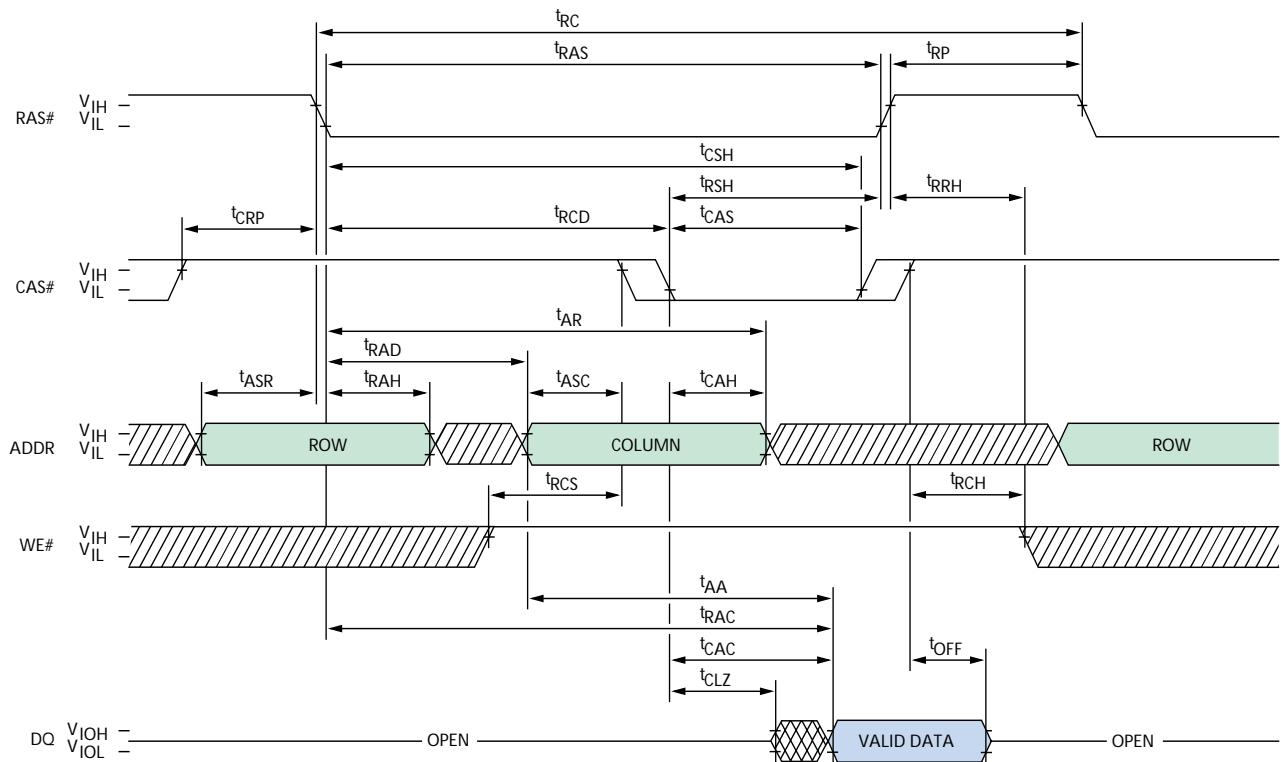
NOTES

1. All voltages referenced to Vss.
2. This parameter is sampled. Vcc = +3.3V or 5.0V; f = 1 MHz.
3. Icc is dependent on output loading and cycle rates. Specified values are obtained with minimum cycle time and the outputs open.
4. Enables on-chip refresh and address counters.
5. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range is ensured.
6. An initial pause of 100 μ s is required after power-up, followed by eight RAS# refresh cycles (RAS#-ONLY or CBR with WE# HIGH), before proper device operation is ensured. The eight RAS# cycle wake-ups should be repeated any time the tREF refresh requirement is exceeded.
7. AC characteristics assume tT = 5ns.
8. VIH (MIN) and Vil (MAX) are reference levels for measuring timing of input signals. Transition times are measured between VIH and Vil (or between Vil and VIH).
9. In addition to meeting the transition rate specification, all input signals must transit between VIH and Vil (or between Vil and VIH) in a monotonic manner.
10. If CAS# = VIH, data output is High-Z.
11. If CAS# = Vil, data output may contain data from the last valid READ cycle.
12. Measured with a load equivalent to two TTL gates, 100pF and VOL = 0.8V and VOH = 2V.
13. If CAS# is LOW at the falling edge of RAS#, Q will be maintained from the previous cycle. To initiate a new cycle and clear the data-out buffer, CAS# must be pulsed HIGH for tCP.
14. The tRCD (MAX) limit is no longer specified. tRCD (MAX) was specified as a reference point only. If tRCD was greater than the specified tRCD (MAX) limit, then access time was controlled exclusively by tCAC (tRAC [MIN] no longer applied). With or without the tRCD limit, tAA and tCAC must always be met.
15. The tRAD (MAX) limit is no longer specified. tRAD (MAX) was specified as a reference point only. If tRAD was greater than the specified tRAD (MAX) limit, then access time was con-

trolled exclusively by tAA (tRAC and tCAC no longer applied). With or without the tRAD (MAX) limit, tAA, tRAC, and tCAC must always be met.

16. Either tRCH or tRRH must be satisfied for a READ cycle.
17. tOFF (MAX) defines the time at which the output achieves the open circuit condition and is not referenced to VOH or VOL.
18. tWCS, tRWD, tAWD, and tCWD are not restrictive operating parameters. tWCS applies to EARLY WRITE cycles. tRWD, tAWD, and tCWD apply to READ-MODIFY-WRITE cycles. If tWCS \geq tWCS (MIN), the cycle is an EARLY WRITE cycle and the data output will remain an open circuit throughout the entire cycle. If tRWD \geq tRWD (MIN), tAWD \geq tAWD (MIN), and tCWD \geq tCWD (MIN), the cycle is a READ-MODIFY-WRITE and the data output will contain data read from the selected cell. If neither of the above conditions is met, the state of data-out is indeterminate. OE# held HIGH and WE# taken LOW after CAS# goes LOW result in a LATE WRITE (OE#-controlled) cycle. tWCS, tRWD, tCWD, and tAWD are not applicable in a LATE WRITE cycle.
19. These parameters are referenced to CAS# leading edge in EARLY WRITE cycles and WE# leading edge in LATE WRITE or READ-MODIFY-WRITE cycles.
20. If OE# is tied permanently LOW, LATE WRITE, or READ-MODIFY-WRITE operations are not permissible and should not be attempted.
21. A HIDDEN REFRESH may also be performed after a WRITE cycle. In this case, WE# = LOW and OE# = HIGH.
22. The 3ns minimum is a parameter guaranteed by design.
23. Column address changed once each cycle.
24. VIH overshoot: VIH (MAX) = Vcc + 2V for a pulse width \leq 10ns, and the pulse width cannot be greater than one third of the cycle rate. Vil undershoot: Vil (MIN) = -2V for a pulse width \leq 10ns, and the pulse width cannot be greater than one third of the cycle rate.

READ CYCLE



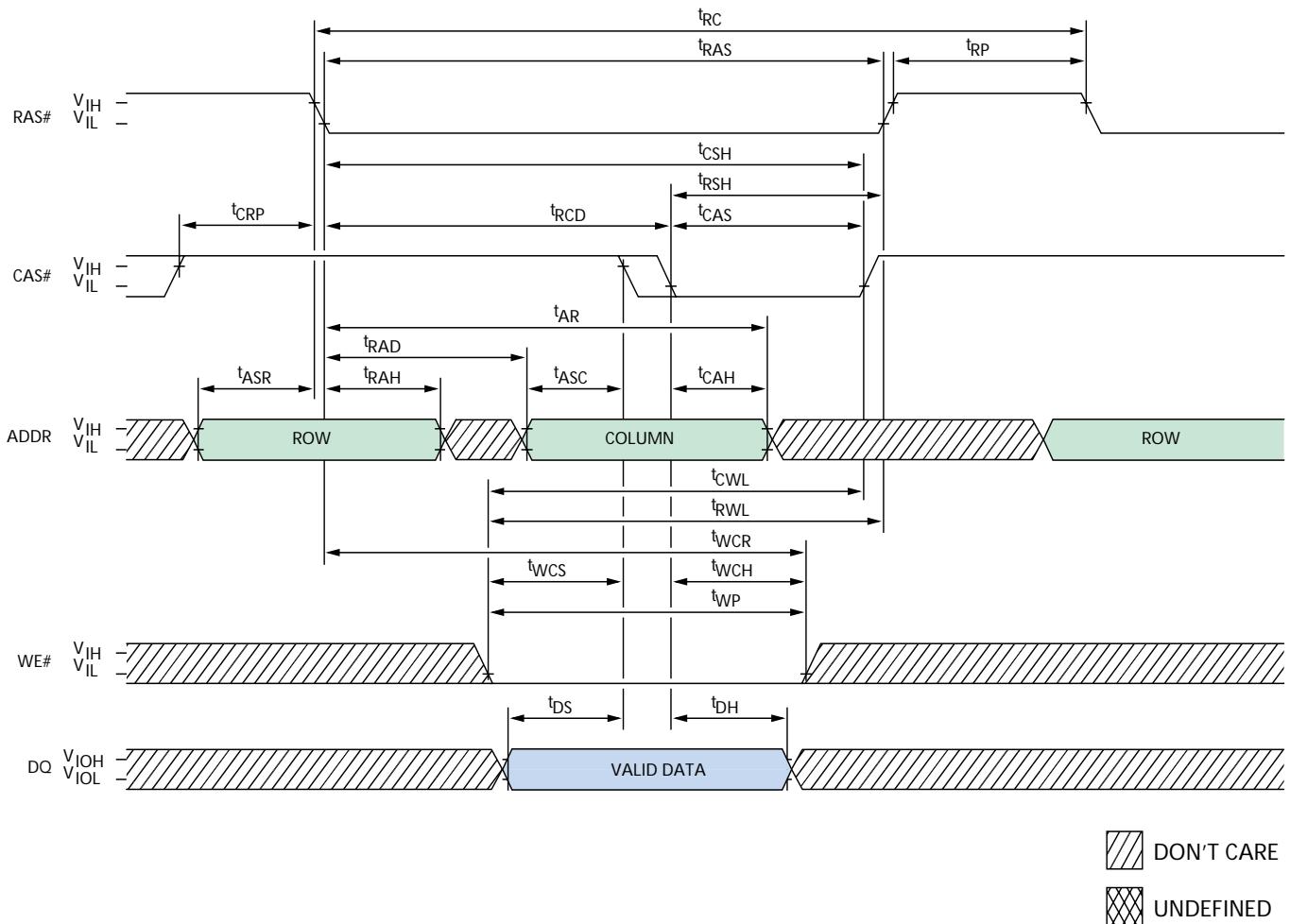
DON'T CARE

UNDEFINED

TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{OD}	0	12	0	15	ns
t _{OE}		12		15	ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{OFF}	0	12	0	15	ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RAS}	50	10,000	60	10,000	ns
t _{RC}	84		104		ns
t _{RCD}	11		14		ns
t _{RCH}	0		0		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RRH}	0		0		ns
t _{RSH}	13		15		ns

EARLY WRITE CYCLE


DON'T CARE

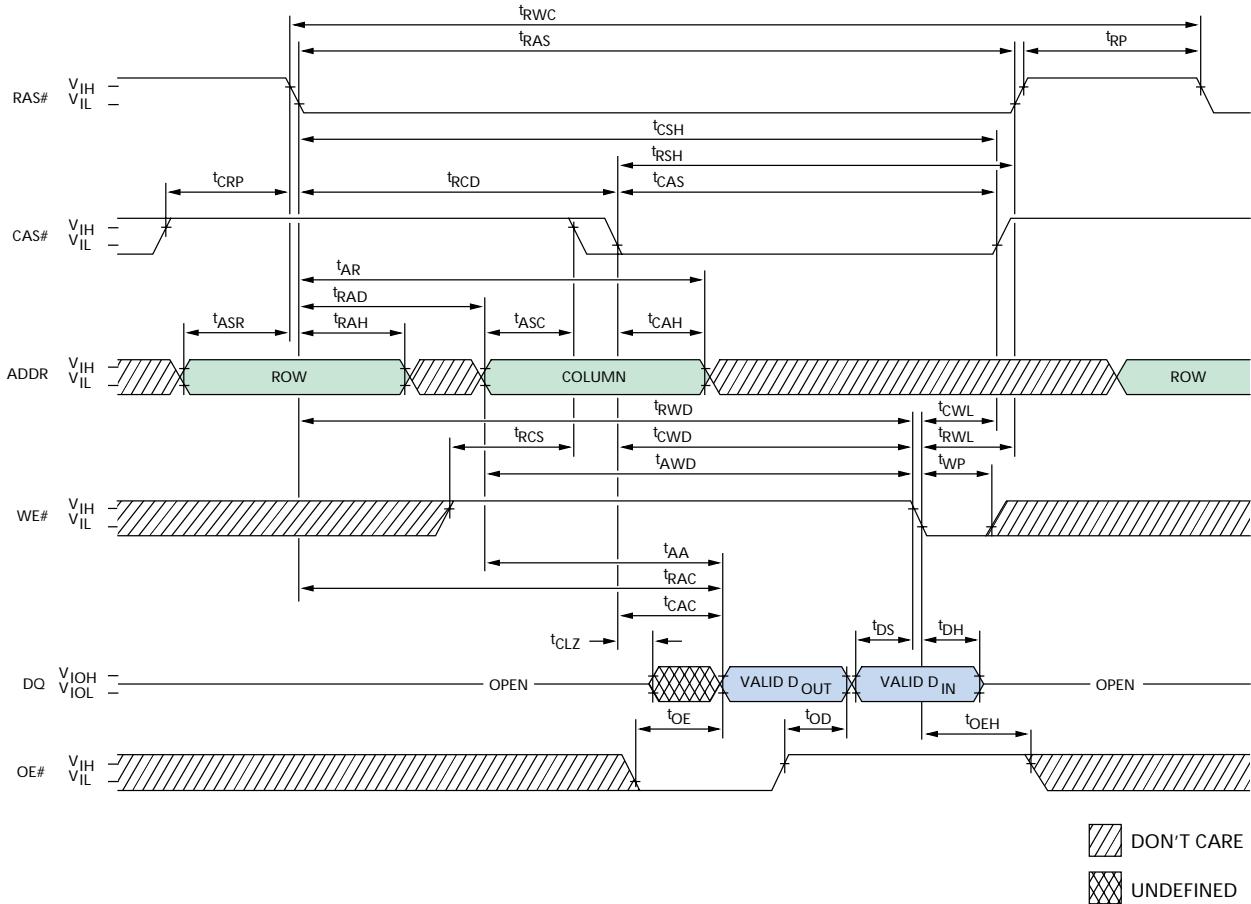
UNDEFINED

TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns
t _{RAD}	9		12		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RAH}	9		10		ns
t _{RAS}	50	10,000	60	10,000	ns
t _{RC}	84		104		ns
t _{RCD}	11		14		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWL}	13		15		ns
t _{WCH}	8		10		ns
t _{WCR}	38		45		ns
t _{WCS}	0		0		ns
t _{WP}	5		5		ns

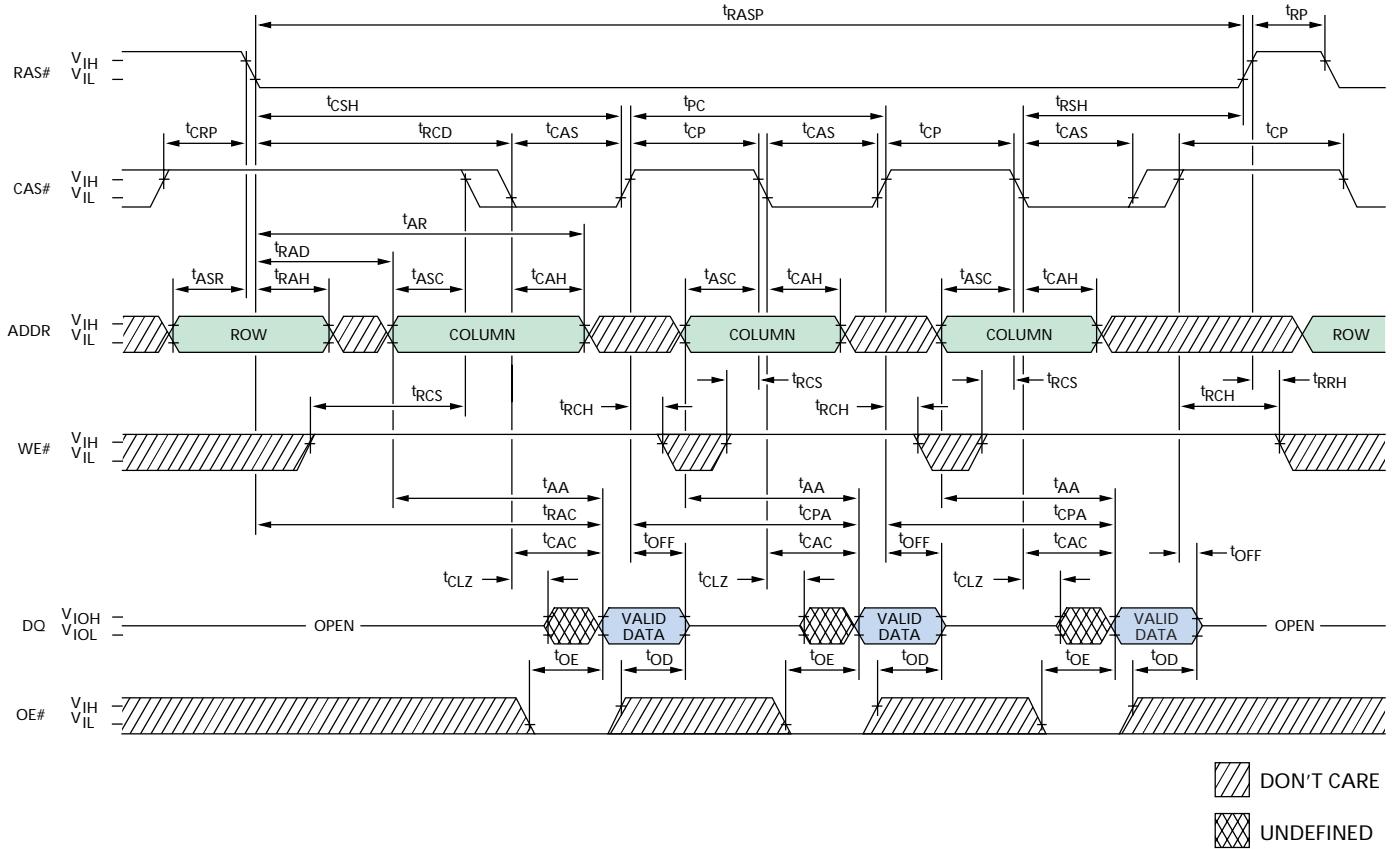
READ-WRITE CYCLE (LATE WRITE and READ-MODIFY-WRITE cycles)



TIMING PARAMETERS

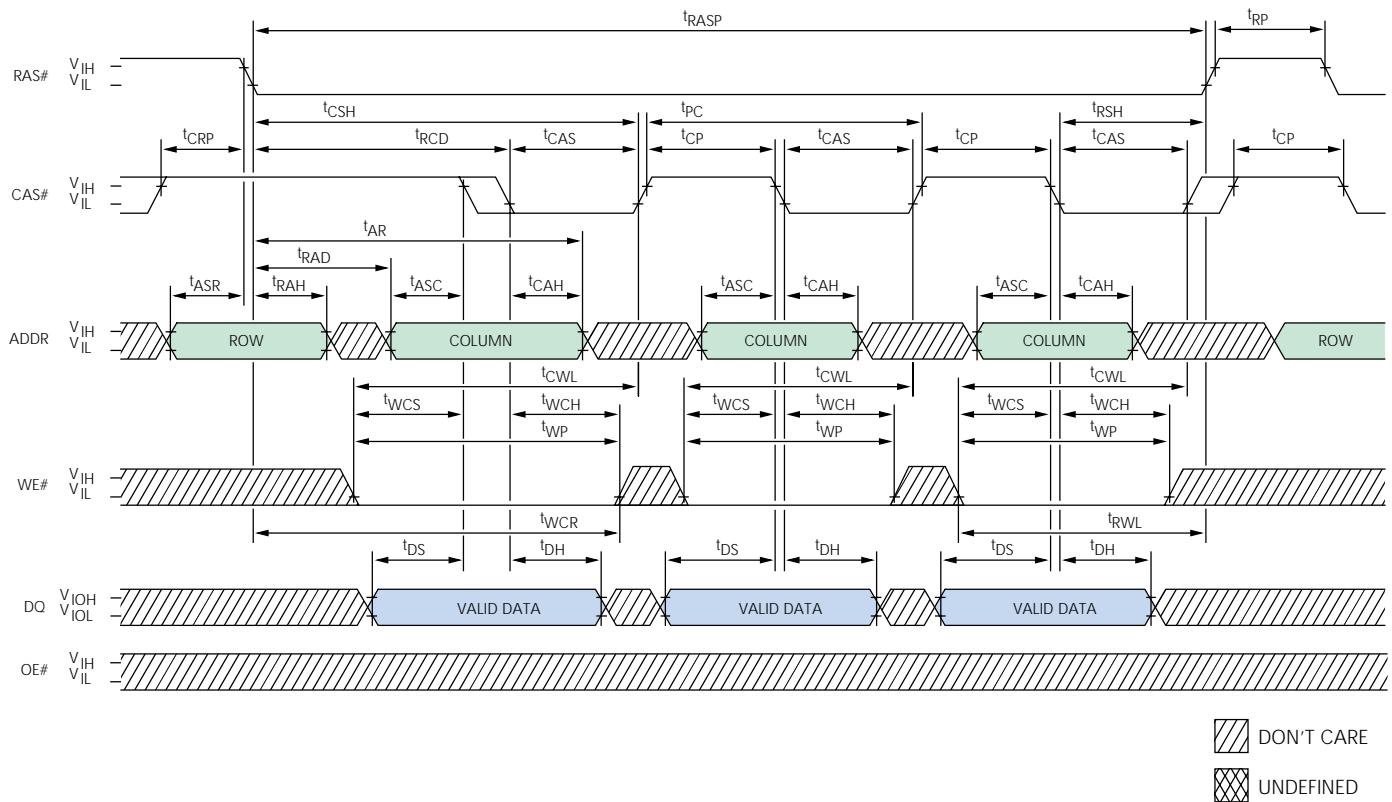
SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{AWD}	42		49		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWD}	28		35		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{OD}	0	12	0	15	ns
t _{OE}		12		15	ns
t _{OEH}	8		10		ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RAS}	50	10,000	60	10,000	ns
t _{RCD}	11		14		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWC}	116		140		ns
t _{RWD}	67		79		ns
t _{RWL}	13		15		ns
t _{WP}	5		5		ns

FAST-PAGE-MODE READ CYCLE

TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CP}	8		10		ns
t _{CPA}		28		35	ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{OD}	0	12	0	15	ns

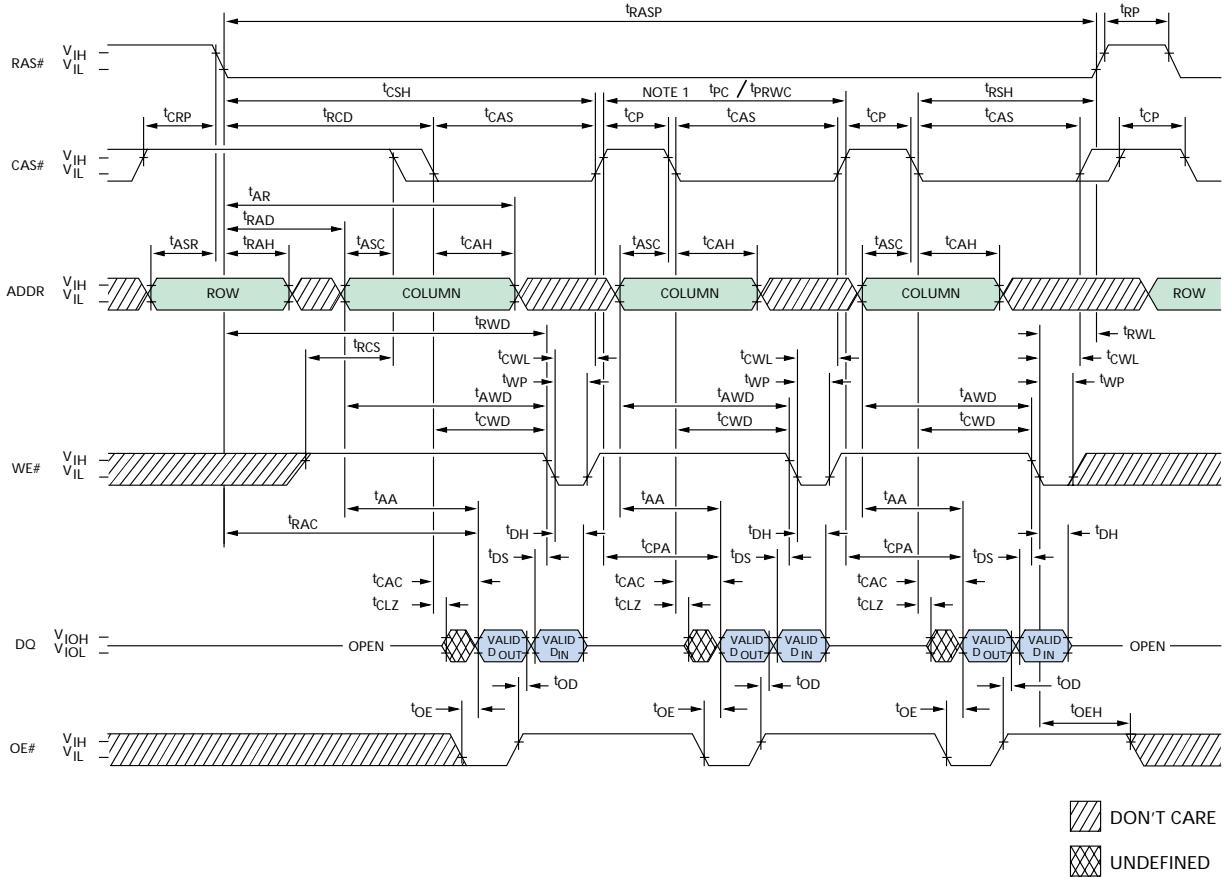
SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{OE}				15	ns
t _{OFF}	0	12	0	15	ns
t _{PC}	20		25		ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RCH}	0		0		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RRH}	0		0		ns
t _{RSH}	13		15		ns

FAST-PAGE-MODE EARLY WRITE CYCLE

TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns
t _{PC}	20		25		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWL}	13		15		ns
t _{WCH}	8		10		ns
t _{WCR}	38		45		ns
t _{WCS}	0		0		ns
t _{WP}	5		5		ns

FAST-PAGE-MODE READ-WRITE CYCLE (LATE WRITE and READ-MODIFY-WRITE cycles)



DON'T CARE
 UNDEFINED

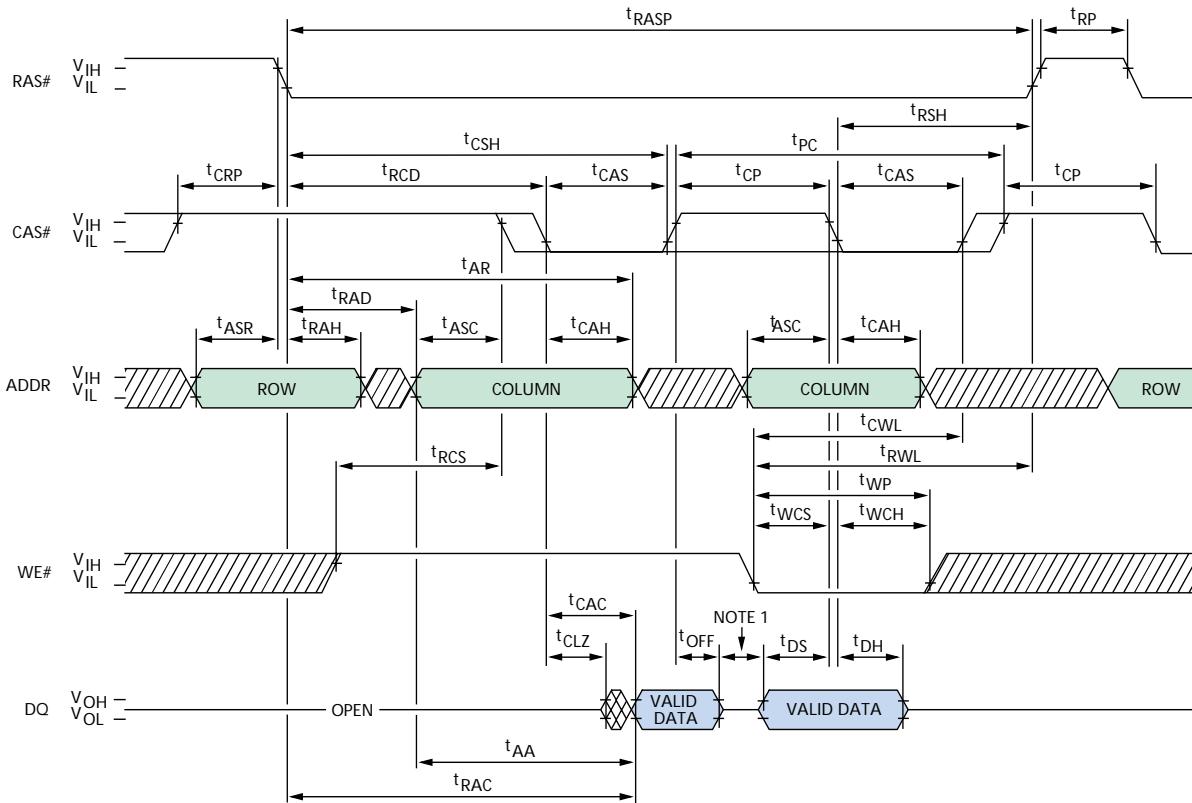
TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{AWD}	42		49		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CP}	8		10		ns
t _{CPA}		28		35	ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWD}	28		35		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{OD}	0	12	0	15	ns
t _{OE}			12		ns
t _{OEH}	8		10		ns
t _{PC}	20		25		ns
t _{PRWC}	47		56		ns
t _{RAC}			50		ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWD}	67		79		ns
t _{RWL}	13		15		ns
t _{WP}	5		5		ns

NOTE: 1. t_{PC} is for LATE WRITE only.

FAST-PAGE-MODE READ EARLY WRITE CYCLE (Pseudo READ-MODIFY-WRITE)



DON'T CARE

UNDEFINED

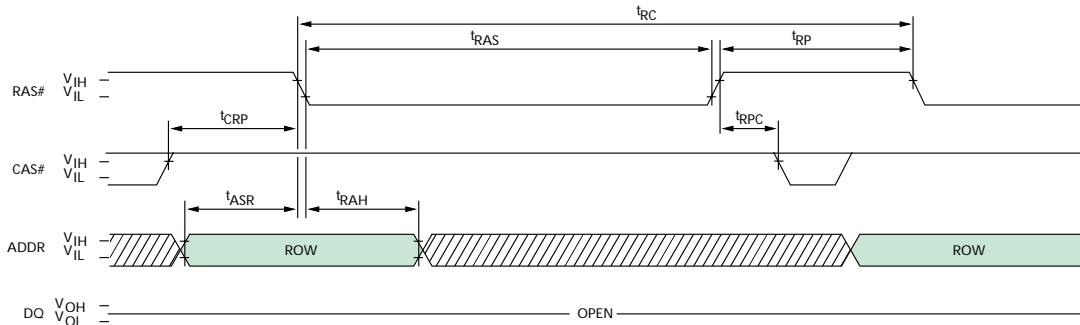
TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns

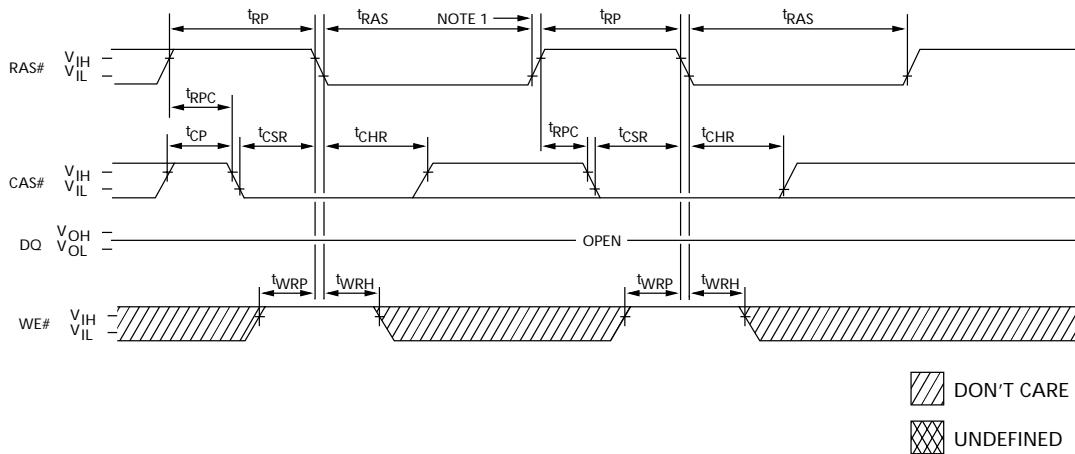
SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{OFF}	0	12	0	15	ns
t _{PC}	20		25		ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWL}	13		15		ns
t _{WCH}	8		10		ns
t _{WCS}	0		0		ns
t _{WP}	5		5		ns

NOTE: 1. Do not drive data prior to tristate.

RAS#-ONLY REFRESH CYCLE (OE# and WE# = DON'T CARE)



CBR REFRESH CYCLE (Addresses and OE# = DON'T CARE)



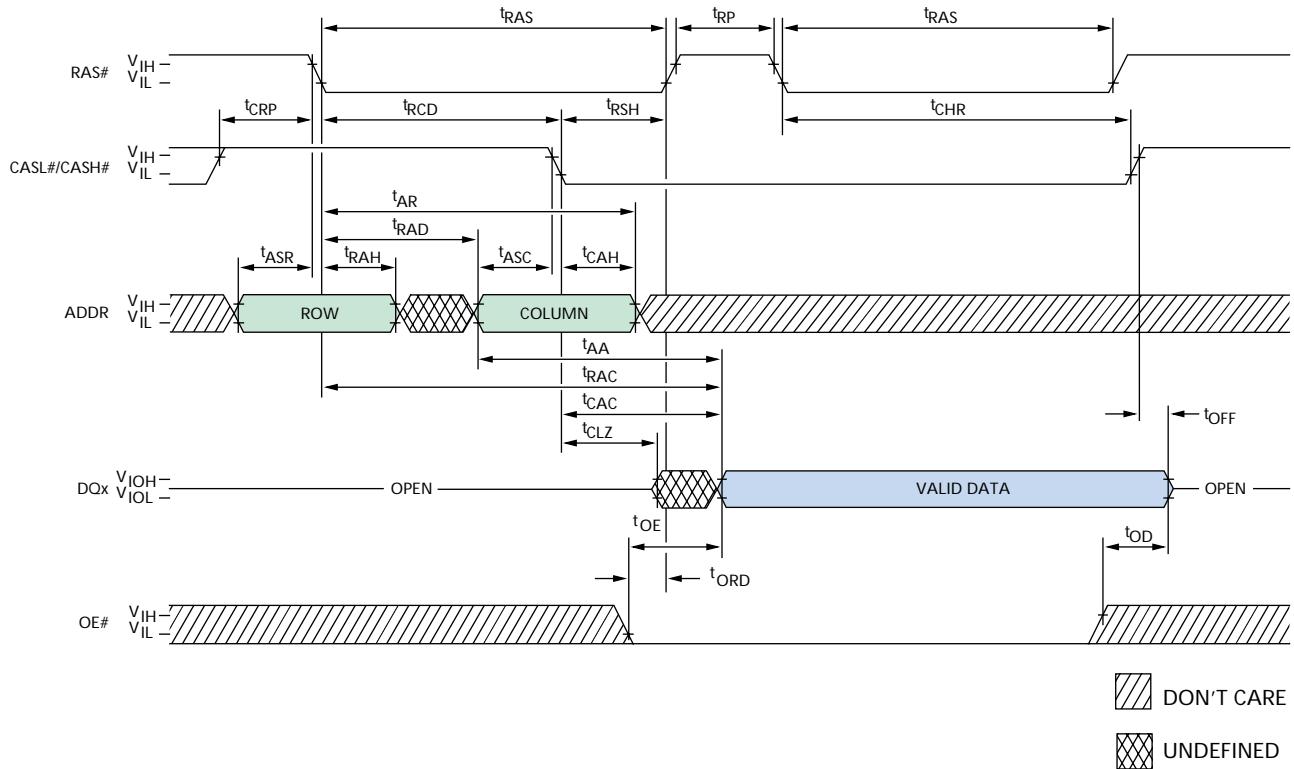
TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{ASR}	0		0		ns
t _{CHR}	8		10		ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns
t _{CSR}	5		5		ns
t _{RAH}	9		10		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RAS}	50	10,000	60	10,000	ns
t _{RC}	84		104		ns
t _{RP}	30		40		ns
t _{RPC}	5		5		ns
t _{WRH}	8		10		ns
t _{WRP}	8		10		ns

NOTE: 1. End of CBR Refresh cycle.

HIDDEN REFRESH CYCLE¹ (WE# = HIGH; OE# = LOW)



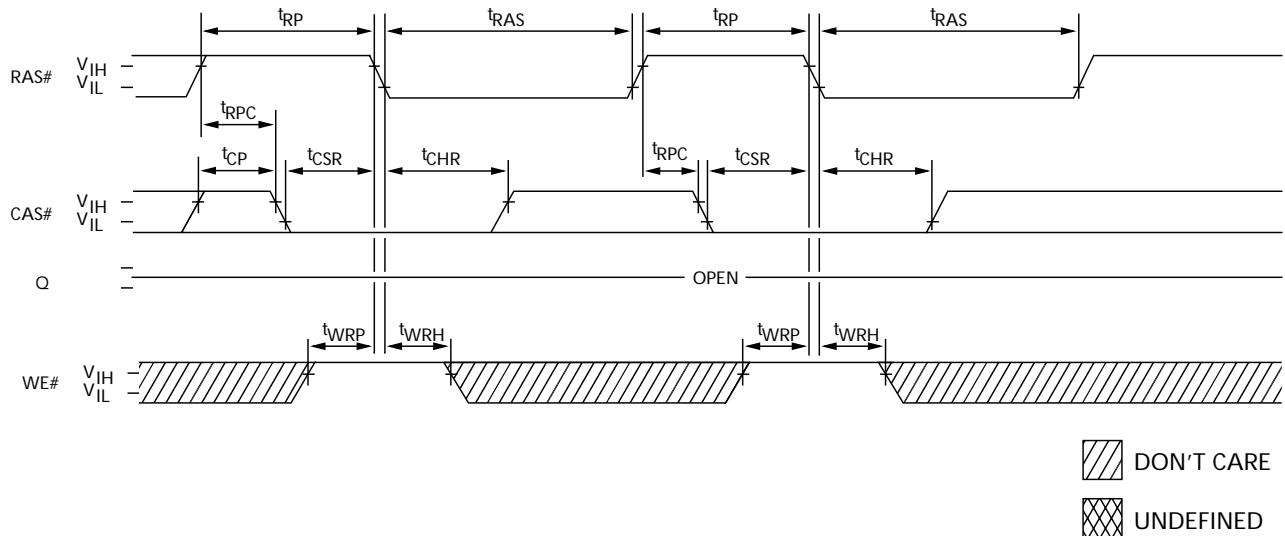
TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
tAA		25		30	ns
tAR	38		45		ns
tASC	0		0		ns
tASR	0		0		ns
tCAC		13		15	ns
tCAH	8		10		ns
tCHR	8		10		ns
tCLZ	0		0		ns
tCRP	5		5		ns
tOD	0	12	0	15	ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
tOE		12		15	ns
tOFF	0	12	0	15	ns
tORD	0		0		ns
tRAC		50		60	ns
tRAD	9		12		ns
tRAH	9		10		ns
tRAS	50	10,000	60	10,000	ns
tRCD	11		14		ns
tRP	30		40		ns
tRSH	13		15		ns

NOTE: 1. A HIDDEN REFRESH may also be performed after a WRITE cycle. In this case, WE# is LOW and OE# is HIGH.

SELF REFRESH CYCLE (Addresses and OE# = DON'T CARE)

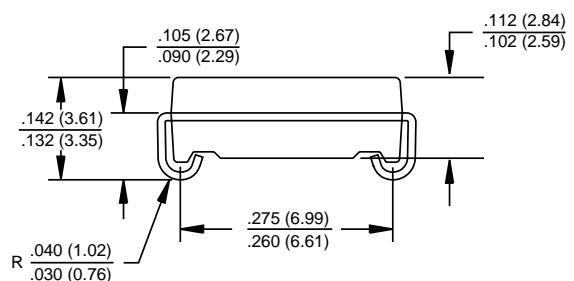
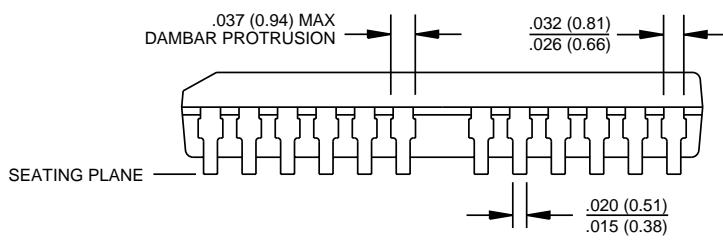
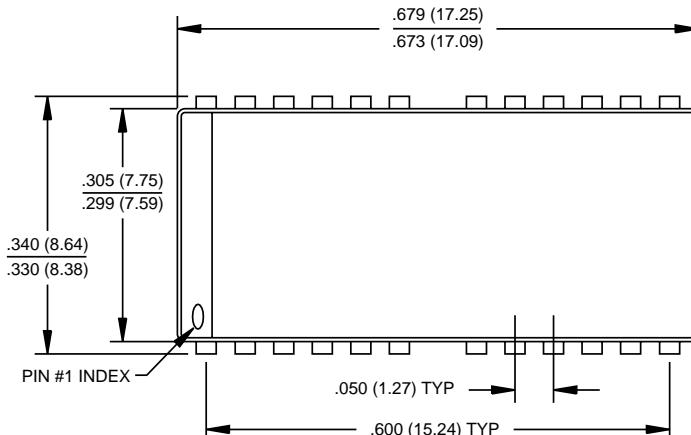


TIMING PARAMETERS

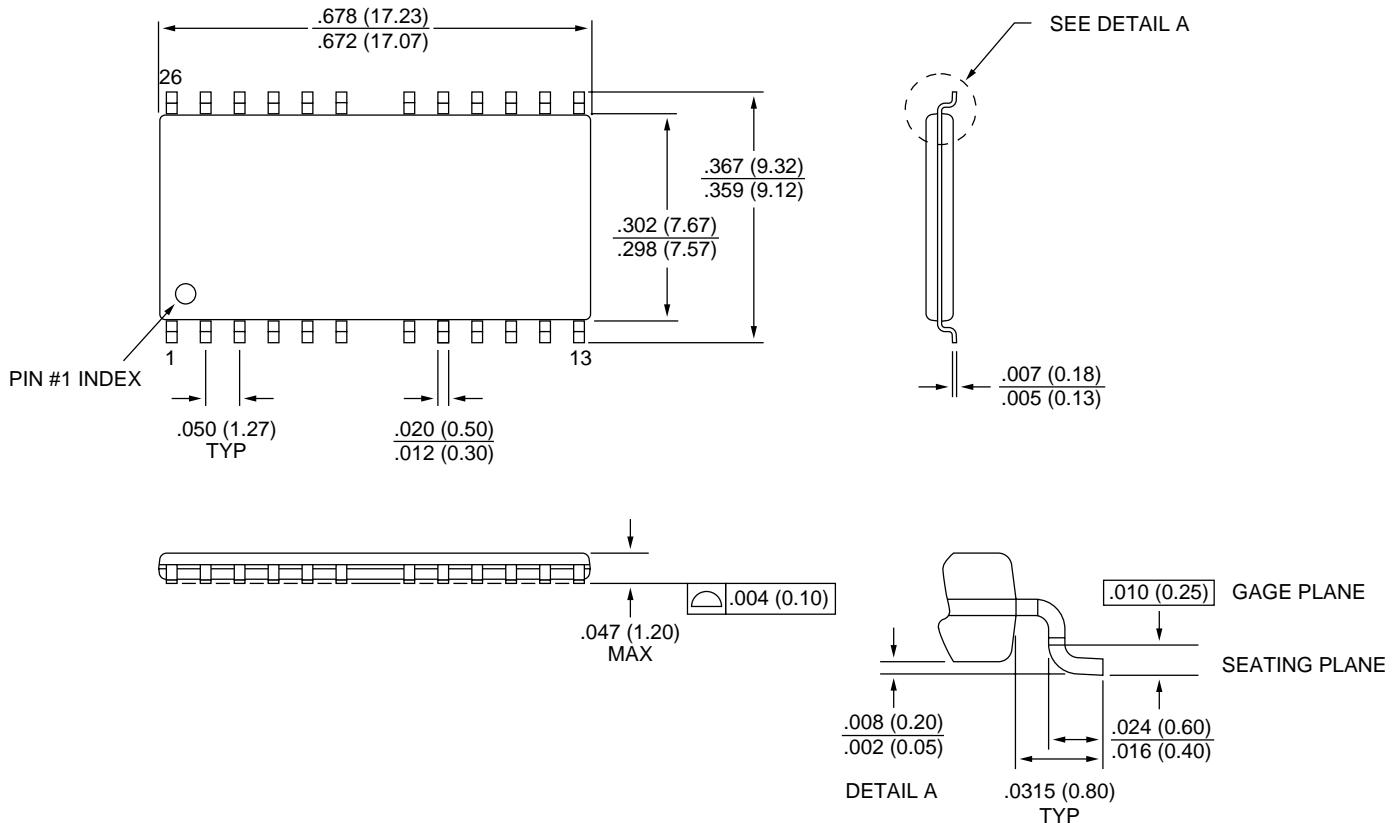
SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{CHD}	15		15		ns
t _{CP}	8		10		ns
t _{CSR}	5		5		ns
t _{RASS}	100		100		μs
t _{RP}	30		40		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RPC}	5		5		ns
t _{RPS}	90		105		ns
t _{WRH}	8		10		ns
t _{WRP}	8		10		ns

NOTE: 1. Once t_{RASS} (MIN) is met and RAS# remains LOW, the DRAM will enter self refresh mode.
 2. Once t_{RPS} is satisfied, a complete burst of all rows should be executed if RAS#-only or burst CBR refresh is used.

24/26-PIN PLASTIC SOJ (300 mil)


- NOTE:**
- All dimensions in inches (millimeters) $\frac{\text{MAX}}{\text{MIN}}$ or typical where noted.
 - Package width and length do not include mold protrusion; allowable mold protrusion is .01" per side.

24/26-PIN PLASTIC TSOP (300 mil)


NOTE:

- All dimensions in inches (millimeters) $\frac{\text{MAX}}{\text{MIN}}$ or typical where noted.
- Package width and length do not include mold protrusion; allowable mold protrusion is .01" per side.



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помошь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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